

Silicon PNP Power Transistors

2SB1258

DESCRIPTION

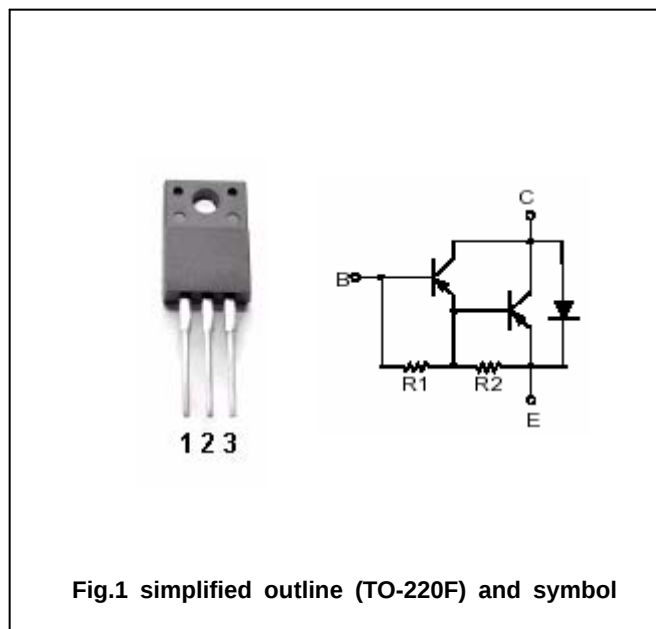
- With TO-220F package
- Complement to type 2SD1785
- High DC current gain
- DARLINGTON

APPLICATIONS

- Driver for solenoid ,relay and motor and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_{CM}	Collector current-peak		-10	A
I_B	Base current		-1	A
P_C	Collector power dissipation	$T_C=25$	30	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA$; $I_B = 0$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3A$; $I_B = -6mA$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -3A$; $I_B = -6mA$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -100V$; $I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -6V$; $I_C = 0$			-10	μA
h_{FE}	DC current gain	$I_C = -3A$; $V_{CE} = -2V$	1000			
f_T	Transition frequency	$I_E = 0.2A$; $V_{CE} = -12V$		100		MHz
C_{OB}	Collector output capacitance	$I_E = 0$; $f = 1MHz$; $V_{CB} = -10V$		100		pF

Switching times

t_{on}	Turn-on time	$I_C = -3A$; $I_{B1} = -I_{B2} = -6mA$ $V_{CC} = -30V$, $R_L = 10\Omega$		0.6		μs
t_s	Storage time			1.6		μs
t_f	Fall time			0.5		μs

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PACKAGE OUTLINE

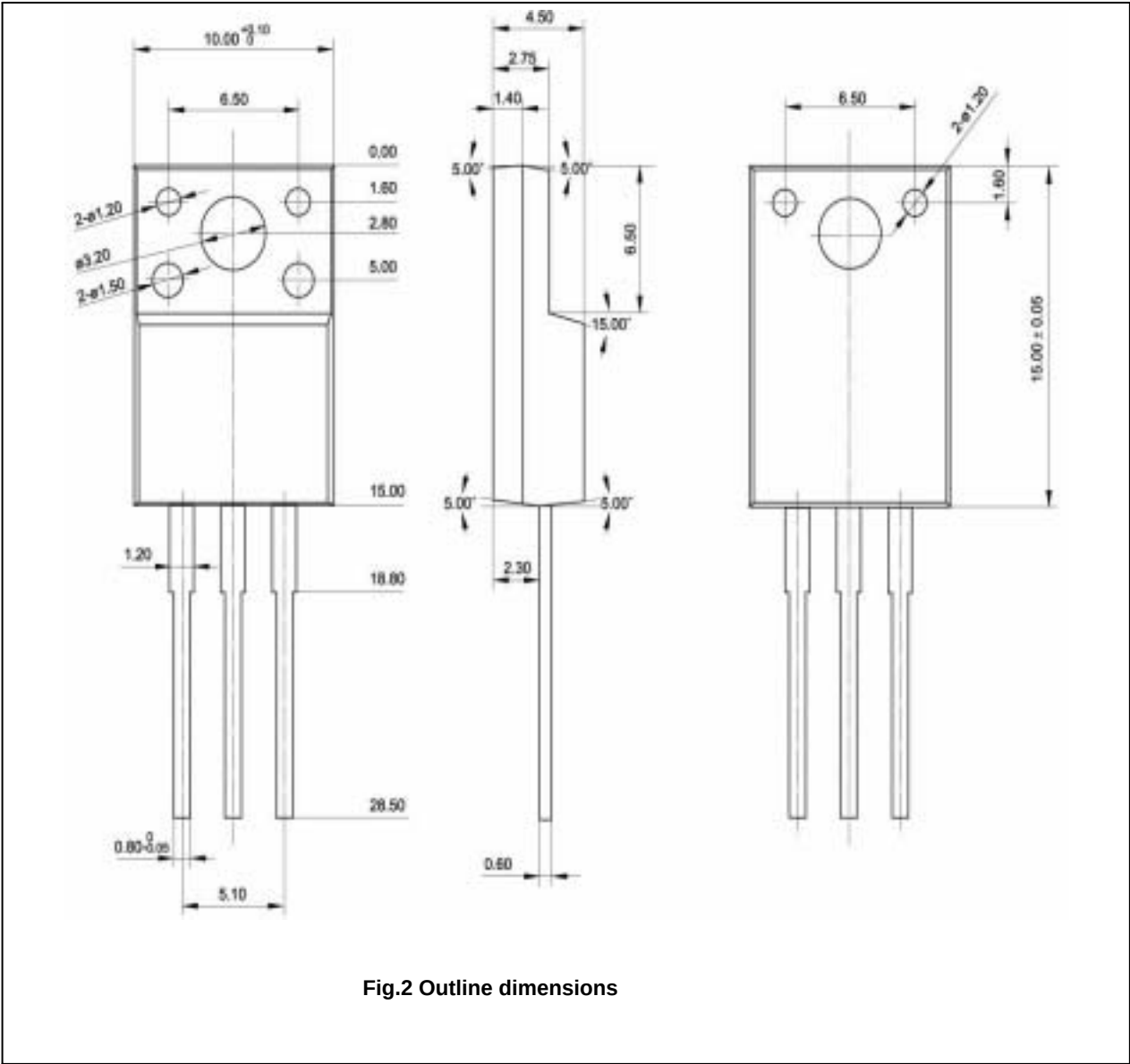


Fig.2 Outline dimensions